**TENTATIVE** 

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

## **HN3C14F**

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

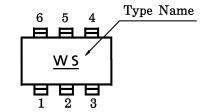
• Including Two Devices in SM6 (Super Mini Type with 6 Leads)

## MAXIMUM RATINGS (Ta = 25°C)

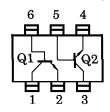
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$v_{CBO}$	20	V
Collector-Emitter Voltage	$v_{CEO}$	10	V
Emitter-Base Voltage	$V_{ m EBO}$	3	V
Collector Current	$I_{\mathbf{C}}$	60	mA
Base Current	$I_{\mathrm{B}}$	30	mA
Collector Power Dissipation	PC*	300	mW
Junction Temperature	$T_{j}$	125	°C
Storage Temperature Range	$T_{ m stg}$	-55~125	°C

\*: Total

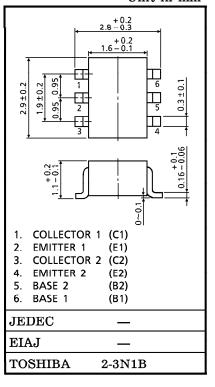
**MARKING** 



PIN ASSIGNMENT (TOP VIEW)



Unit in mm



## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=10V, I_{E}=0$	_	_	1	μA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=1V, I_{C}=0$		1	1	$\mu$ A
DC Current Gain	$\mathbf{h_{FE}}$	$V_{CE}=5V, I_{C}=5mA$	80	_	240	_
Transition Frequency	$ m f_{T}$	$V_{CE}=5V, I_{C}=5mA$	3	5	_	GHz
Insertion Gain	$ \mathrm{S}_{21\mathrm{e}} ^2$	$V_{CE}=5V$ , $I_{C}=5mA$ , $f=1GHz$	6	10	<u> </u>	dB
Reverse Transfer Capacitance Q1	$\mathrm{C_{re}}$	V <sub>CB</sub> =5V, I <sub>E</sub> =0, f=1MHz (Note)	ı	0.9	_	рF
Reverse Transfer Capacitance Q2	$\mathrm{C_{re}}$			0.7	1.1	рF

(Note) Cre is measured by 3 terminal method capacitance bridge.

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